

BUK764R0-75C

N-channel TrenchMOS standard level FET Rev. 2 — 26 April 2011

Product data sheet

1. **Product profile**

1.1 General description

Standard level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC-Q101 compliant
- Avalanche robust

- Suitable for standard level gate drive
- Suitable for thermally demanding environment due to 175 °C rating

1.3 Applications

- 12 V Motor, lamp and solenoid loads
- High performance automotive power systems
- High performance Pulse Width Modulation (PWM) applications

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	75	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u> ; see <u>Figure 4</u>	[1][2]	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	333	W



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{\text{Figure 8}};$	-	3.4	4	mΩ
I _{GSS}	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V};$ $T_j = 25 \text{ °C}$	-	2	100	nA
Avalanche	Avalanche ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 100 \text{ A; } V_{\text{sup}} \leq 75 \text{ V;} \\ R_{\text{GS}} &= 50 \Omega; V_{\text{GS}} = 10 \text{ V;} \\ T_{j(\text{init})} &= 25 ^{\circ}\text{C; unclamped} \end{split}$	-	-	630	mJ

^[1] Refer to document 9397 750 12572 for further information.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain[1]	mb	D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

^[1] It is not possible to make a connection to pin 2 of the SOT404 package.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK764R0-75C	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

^[2] Continuous current is limited by package.

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	75	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	75	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Sign}};$	[1][2]	-	100	Α
		see Figure 4	[1][3]	-	199	Α
		$T_{mb} = 100 ^{\circ}C; V_{GS} = 10 V; see \underline{Figure 1}$	[1][2]	-	100	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; see Figure 4		-	797	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	333	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	n diode					
Is	source current	T _{mb} = 25 °C	[3][1]	-	199	Α
			[3][2]	-	100	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	797	Α
Avalanche ru	uggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 100 A; $V_{sup} \le 75$ V; R_{GS} = 50 Ω ; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	630	mJ
E _{DS(AL)R}	repetitive drain-source avalanche energy	see Figure 3	[4][5] [6][7]	-	-	J

^[1] Refer to document 9397 750 12572 for further information.

^[2] Continuous current is limited by package.

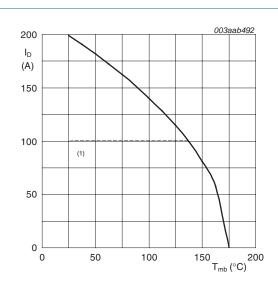
^[3] Current is limited by power dissipation chip rating.

^[4] Maximum value not quoted. Repetitive rating defined in avalanche rating figure.

^[5] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

^[6] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

^[7] Refer to application note AN10273 for further information.

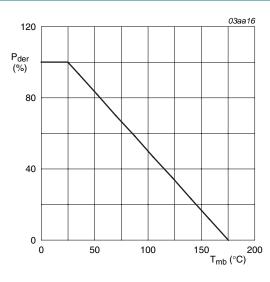


 $V_{\it GS} \geq 10 \ V \label{eq:VGS}$ (1) Capped at 100 A due to package.

function of mounting base temperature

(1) Capped at 100 A due to package.

Fig 1. Normalized continuous drain current as a



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature

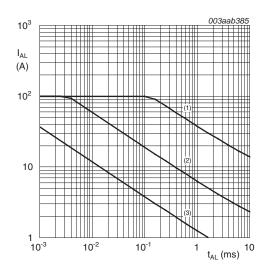
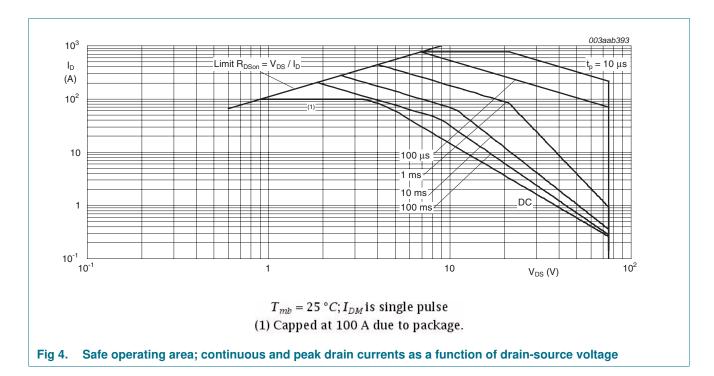


Fig 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time.



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	0.45	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint	[1] -	50	-	K/W

^[1] Mounted on a printed-circuit board; vertical in still air.

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	70	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	75	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see <u>Figure 5</u> ; see <u>Figure 6</u>	2	3	4	V
V _{GSth}	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 175 \text{ °C}$; see <u>Figure 5</u> ; see <u>Figure 6</u>	1	-	-	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see <u>Figure 5</u> ; see <u>Figure 6</u>	-	-	4.4	V
I _{DSS}	drain leakage current	$V_{DS} = 75 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see <u>Figure 7</u> ; see <u>Figure 8</u>	-	-	8.4	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 7</u> ; see <u>Figure 8</u>	-	3.4	4	mΩ
I_{DSS}	drain leakage current	$V_{DS} = 75 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
Dynamic	characteristics					
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}$; $V_{DS} = 60 \text{ V}$; $V_{GS} = 10 \text{ V}$;	-	142	-	nC
Q_{GS}	gate-source charge	see Figure 9	-	36	-	nC
Q_{GD}	gate-drain charge		-	67	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25 \text{ A}$; $V_{DS} = 60 \text{ V}$; see Figure 9	-	5	-	V
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	8744	11659	рF
C _{oss}	output capacitance	$T_j = 25 ^{\circ}C$; see Figure 10	-	923	1108	рF
C _{rss}	reverse transfer capacitance		-	579	793	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	65	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega$	-	133	-	ns
$t_{d(off)}$	turn-off delay time		-	146	-	ns
t _f	fall time		-	119	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to centre of die	-	2.5	-	nΗ
L _S	internal source inductance	from source lead to source bonding pad	-	7.5	-	nΗ
Source-d	rain diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 11</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	83	-	ns
Q _r	recovered charge	$V_{DS} = 25 \text{ V}$	-	155	-	nC

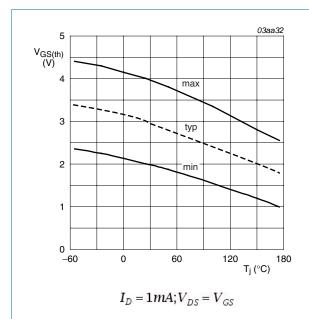
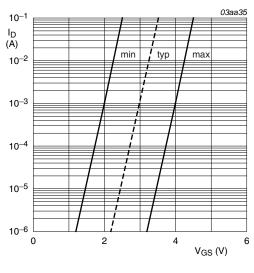


Fig 5. Gate-source threshold voltage as a function of junction temperature



 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$

Fig 6. Sub-threshold drain current as a function of gate-source voltage

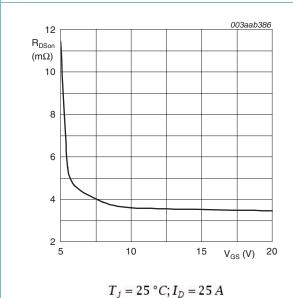


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

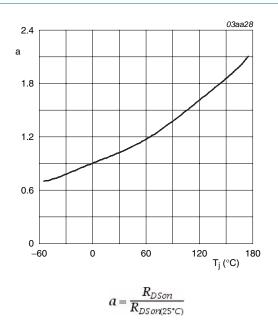


Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature

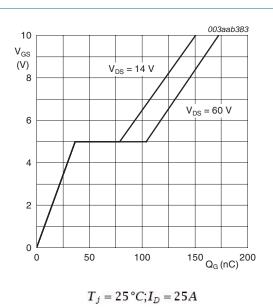
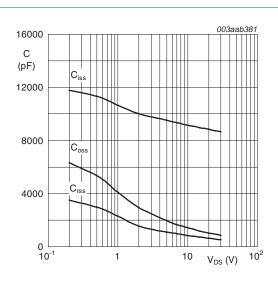


Fig 9. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$

Fig 10. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

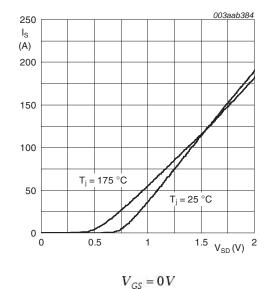


Fig 11. Source current as a function of source-drain diode; typical values

7. Package outline

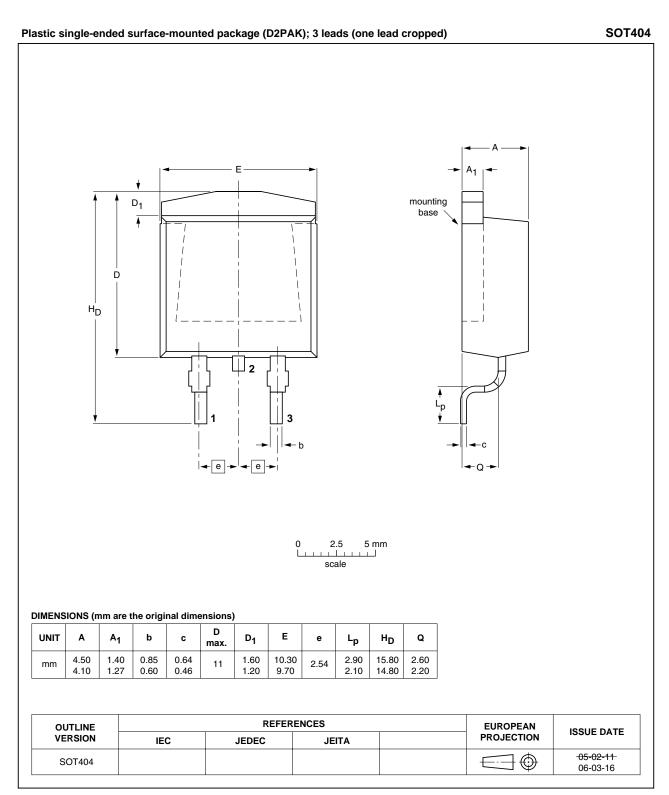


Fig 12. Package outline SOT404 (D2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BUK764R0-75C v.2	20110426	Product data sheet	-	BUK764R0-75C_1		
Modifications:	 The format of of NXP Semio 		designed to comply with	y with the new identity guidelines		
	 Legal texts ha 	ve been adapted to the new	company name where	appropriate.		
BUK764R0-75C_1	20060817	Product specification	-	-		

10 of 13

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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BUK764R0-75C

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N-channel TrenchMOS standard level FET

11. Contents

1	Product profile
1.1	General description
1.2	Features and benefits1
1.3	Applications
1.4	Quick reference data1
2	Pinning information2
3	Ordering information
4	Limiting values
5	Thermal characteristics5
6	Characteristics6
7	Package outline
8	Revision history10
9	Legal information11
9.1	Data sheet status
9.2	Definitions11
9.3	Disclaimers
9.4	Trademarks12
10	Contact information 10